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捷多邦,专业PCBISN54AH论下的78章SN574AHCT373 OCTAL TRANSPARENT D-TYPE LATCHES WITH 3-STATE OUTPUTS

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- EPIC[™] (Enhanced-Performance Implanted CMOS) Process
- Inputs Are TTL-Voltage Compatible
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) DIPs

description

The 'AHCT373 devices are octal-transparent D-type latches. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is low, the Q outputs are latched at the logic levels of the D inputs.

A buffered output-enable (\overline{OE}) input can be used to place the eight outputs in either a normal logic state (high or low) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

SN54AHCT373 J OR W PACKAGE
SN74AHCT373DB, DGV, DW, N, OR PW PACKAGE
(TOP VIEW)

			_	
OE	[1	0 20		cc
1Q	2	19	80	2
1D		18	8)
2D	4	17	70 70)
2Q	5	16	70	כ
3Q	6	15	60	כ
3D	[7	14] 60)
4D	8]	13	5] 5 E)
4Q	9	12	2] 50	כ
GND	[10	11	рие	

SN54AHCT373 ... FK PACKAGE (TOP VIEW)

	10	ą	Ю	V _{CC}	ő			
2D 2Q 3Q 3D 4D	3 5 7 3 9	2	1	20 12	19	18 [17 [16 [15 [14 [8D 7D 7Q 6Q 6D	
	40	GND	Щ	20 I	5D			

OE does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, OE should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54AHCT373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74AHCT373 is characterized for operation from –40°C to 85°C.

	FUNCTION TABLE (each latch)											
	30	INPUTS		OUTPUT								
	OE	LE	D	Q								
S	6 T.	Н	Н	Н								
	L	Н	L	L								
	L	L	Х	Q ₀								
	Н	Х	Х	Z								



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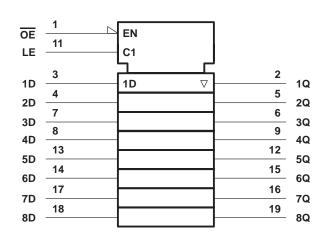
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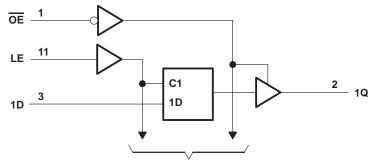
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logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



To Seven Other Channels

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[‡]

Supply voltage range, V_{CC} Input voltage range, V_I (see Note 1) Output voltage range, V_O (see Note 1) Input clamp current, I_{IK} ($V_I < 0$) Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$ Continuous output current, I_O ($V_O = 0$ to V_{CC}) Continuous current through V_{CC} or GND Package thermal impedance, θ_{JA} (see Note 2):	DB package DGV package DW package N package PW package	$\begin{array}{cccc} -0.5 \mbox{ V to 7 V} \\0.5 \mbox{ V to V}_{CC} + 0.5 \mbox{ V} \\20 \mbox{ mA} \\ +20 \mbox{ mA} \\ +25 \mbox{ mA} \\ +25 \mbox{ mA} \\ +75 \mbox{ mA} \\ 58^{\circ} C/W \\ 58^{\circ} C/W \\ 83^{\circ} C/W \\ 83^{\circ} C/W \end{array}$
Storage temperature range, T _{stg}		

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.



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recommended operating conditions (see Note 3)

		SN54AH	CT373	SN74AH	CT373	UNIT
		MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2		2		V
VIL	Low-level input voltage		0.8		0.8	V
VI	Input voltage	0	5.5	0	5.5	V
Vo	Output voltage	0	VCC	0	VCC	V
IOH	High-level output current		-8		-8	mA
IOL	Low-level output current		8		8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		20		20	ns/V
Т _А	Operating free-air temperature	-55	125	-40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	Vee	Т	ן = 25°C	;	SN54AH	СТ373	SN74AH	СТ373	UNIT
PARAMETER	TEST CONDITIONS	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
VOH	I _{OH} = -50 μA	4.5 V	4.4	4.5		4.4		4.4		V
VOH	I _{OH} = –8 mA	4.5 V	3.94			3.8		3.8		v
Ve	I _{OL} = 50 μA	4.5 V			0.1		0.1		0.1	V
VOL	I _{OL} = 8 mA	4.5 V			0.36		0.44		0.44	v
loz	$V_{O} = V_{CC} \text{ or } GND$	5.5 V			±0.25		±2.5		±2.5	μΑ
li li	$V_I = V_{CC}$ or GND	0 V to 5.5 V			±0.1		±1*		±1	μΑ
ICC	$V_{I} = V_{CC} \text{ or GND}, I_{O} = 0$	5.5 V			4		40		40	μΑ
∆lcc‡	One input at 3.4 V, Other inputs at V_{CC} or GND	5.5 V			1.35		1.5		1.5	mA
Ci	$V_I = V_{CC}$ or GND	5 V		4	10				10	pF
Co	$V_{O} = V_{CC} \text{ or } GND$	5 V		9						pF

* On products compliant to MIL-PRF-38535, this parameter is not production tested at $V_{CC} = 0$ V.

[†] This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

timing requirements over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

		T _A = 25°C		SN54AH	CT373	SN74AH	CT373	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
tw	Pulse duration, LE high	6.5		6.5		6.5		ns
t _{su}	Setup time, data before $\overline{LE}\downarrow$	1.5		1.5		1.5		ns
th	Hold time, data after $\overline{\text{LE}}\downarrow$	3.5		3.5		3.5		ns



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PARAMETER	FROM	то	LOAD	Т	ן = 25°C	;	SN54AH	ICT373	SN74AH	CT373	UNIT				
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT				
^t PLH	D	Q	CI = 15 pF		5.1*	8.5*	1*	9.5*	1	9.5	ns				
^t PHL		Q	CL = 15 pr		5.1*	8.5*	1*	9.5*	1	9.5	115				
^t PLH	LE	Q	C _L = 15 pF		7.7*	12.3*	1*	13.5*	1	13.5	ns				
^t PHL		Q	0L = 15 pr		7.7*	12.3*	1*	13.5*	1	13.5	115				
^t PZH		Q	C _I = 15 pF		6.3*	10.9*	1*	12.5*	1	12.5	ns				
^t PZL	UE	Q	0 <u> </u>		6.3*	10.9*	1*	12.5*	1	12.5	115				
^t PHZ	OE	Q	C _L = 15 pF		6*	10.2*	1*	11*	1	11	ns				
^t PLZ		Q	× ×		×		0L = 15 pi		6*	10.2*	1*	11*	1	11	115
^t PLH	D	0	0	Q	C _L = 50 pF		5.9	9.5	1	10.5	1	10.5	ns		
^t PHL		Q	С <u>[</u> = 50 рг		5.9	9.5	1	10.5	1	10.5	115				
^t PLH	LE	Q	C _L = 50 pF		8.5	13.3	1	14.5	1	14.5	ns				
^t PHL		Q	0L = 30 pr		8.5	13.3	1	14.5	1	14.5	115				
^t PZH		Q	$C_{\rm L} = 50 \rm pE$		7.1	11.9	1	13.5	1	13.5	ns				
^t PZL			C _L = 50 pF		7.1	11.9	1	13.5	1	13.5	115				
^t PHZ	OE	Q	C _L = 50 pF		6.8	11.2	1	12	1	12	ns				
^t PLZ			CL = 50 pr		6.8	11.2	1	12	1	12	115				
^t sk(o)			C _L = 50 pF			1**				1	ns				

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

* On products compliant to MIL-PRF-38535, this parameter is not production tested. ** On products compliant to MIL-PRF-38535, this parameter does not apply.

noise characteristics, V_{CC} = 5 V, C_L = 50 pF, T_A = 25^{\circ}C (see Note 4)

	PARAMETER	SN7	4AHCT3	373	UNIT
	FARAMETER	MIN	TYP	MAX	UNIT
VOL(P)	Quiet output, maximum dynamic V _{OL}		0.8	1.2	V
VOL(V)	Quiet output, minimum dynamic V _{OL}		-0.8	-1.2	V
VOH(V)	Quiet output, minimum dynamic V _{OH}	4.1			V
VIH(D)	High-level dynamic input voltage	2			V
V _{IL(D)}	Low-level dynamic input voltage			0.8	V

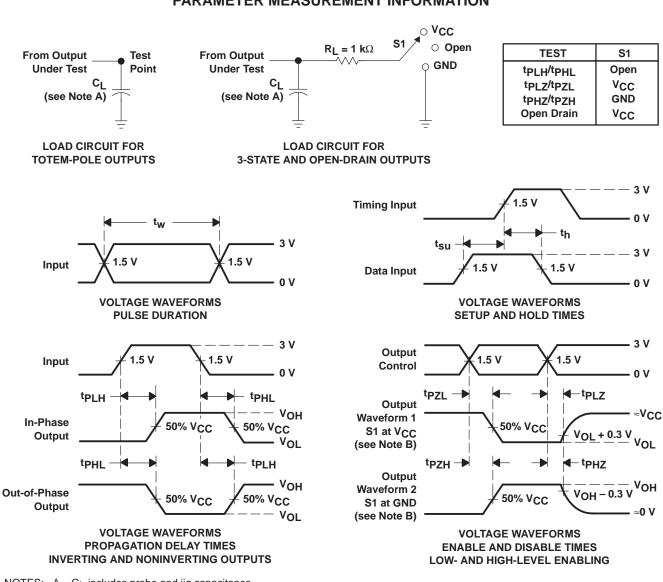
NOTE 4: Characteristics are for surface-mount packages only.

operating characteristics, V_{CC} = 5 V, T_A = 25°C

	PARAMETER		ONDITIONS	TYP	UNIT
Cpd	Power dissipation capacitance	No load,	f = 1 MHz	17	pF



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PARAMETER MEASUREMENT INFORMATION

NOTES: A. CI includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_f \leq 3 ns, t_f \leq 3 ns.

D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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